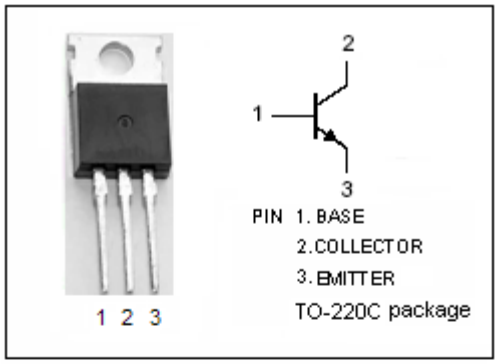
isc Silicon NPN Power Transistor 2SD357



DESCRIPTION

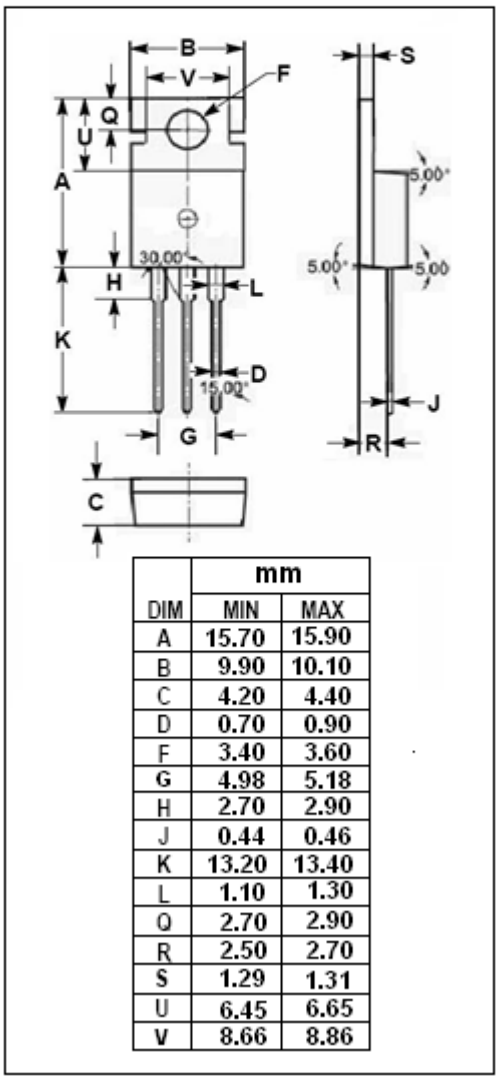
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 100V(Min)
- Good Linearity of h_{FE}
- Complement to Type 2SB527

APPLICATIONS

- Designed for AF high power dirver applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	110	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	0.8	A
P_C	Collector Power Dissipation @ T_a=25℃	1	W
	Collector Power Dissipation @ T_C=25℃	10	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 10mA; R_{BE}= ∞	100			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 1mA; I_E= 0	110			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA; I_C= 0	5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 0.3A; I_B= 30mA			1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 50mA; V_{CE}= 4V		0.7		V
I_{CBO}	Collector Cutoff Current	V_{CB}= 25V; I_E= 0			10	μA
I_{CEO}	Collector Cutoff Current	V_{CE}= 100V; R_{BE}= ∞			1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			10	μA
h_{FE}	DC Current Gain	I_C= 0.3A; V_{CE}= 4V	55		300	

◆ **h_{FE} Classifications**

C	D	E
55-110	90-180	150-300